

To our customers,

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## Old Company Name in Catalogs and Other Documents

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Renesas Electronics website: <http://www.renesas.com>

April 1<sup>st</sup>, 2010  
Renesas Electronics Corporation

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## SWITCHING N-CHANNEL POWER MOS FET

**DESCRIPTION**

The 2SK3570 is N-channel MOS FET device that features a low on-state resistance and excellent switching characteristics, designed for low voltage high current applications such as DC/DC converter with synchronous rectifier.

**FEATURES**

- 4.5V drive available.
- Low on-state resistance,  
 $R_{DS(on)1} = 12 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 24 \text{ A)}$
- Low gate charge  
 $Q_G = 23 \text{ nC TYP. (} V_{DD} = 16 \text{ V, } V_{GS} = 10 \text{ V, } I_D = 48 \text{ A)}$
- Built-in gate protection diode
- Surface mount device available

**ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25°C)**

Drain to Source Voltage (V <sub>GS</sub> = 0 V)	V <sub>DSS</sub>	20	V
Gate to Source Voltage (V <sub>DS</sub> = 0 V)	V <sub>GSS</sub>	±20	V
Drain Current (DC) (T <sub>C</sub> = 25°C)	I <sub>D(DC)</sub>	±48	A
Drain Current (pulse) <b>Note</b>	I <sub>D(pulse)</sub>	±160	A
Total Power Dissipation (T <sub>A</sub> = 25°C)	P <sub>T1</sub>	1.5	W
Total Power Dissipation (T <sub>C</sub> = 25°C)	P <sub>T2</sub>	29	W
Channel Temperature	T <sub>ch</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

**Note** PW ≤ 10 μs, Duty Cycle ≤ 1%

**★ ORDERING INFORMATION**

PART NUMBER	PACKAGE
2SK3570	TO-220AB
2SK3570-S	TO-262
2SK3570-ZK	TO-263
2SK3570-Z	TO-220SMD <b>Note</b>

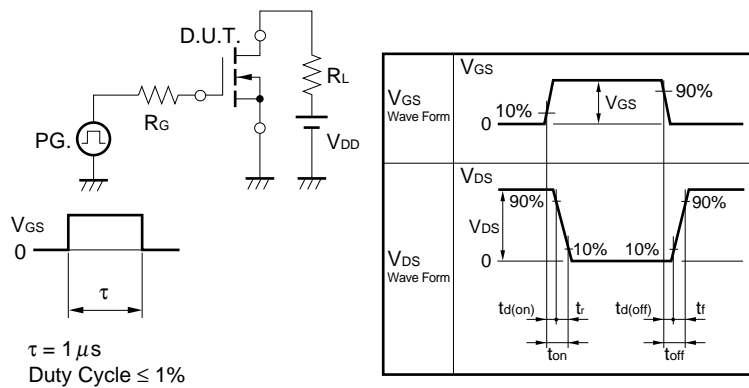
**Note** TO-220SMD package is produced only in Japan.

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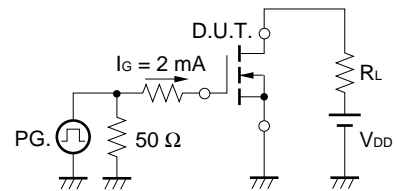
**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C)**

Characteristics	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Zero Gate Voltage Drain Current	I <sub>bss</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V			10	μA
Gate Leakage Current	I <sub>gss</sub>	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V			±10	μA
Gate Cut-off Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	1.5		2.5	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 24 A	8.0			S
Drain to Source On-state Resistance	R <sub>DS(on)1</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 24 A		8.2	12	mΩ
	R <sub>DS(on)2</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 15 A		12.3	22	mΩ
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10 V		930		pF
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V		360		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	f = 1 MHz		250		pF
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 10 V, I <sub>D</sub> = 24 A		13		ns
Rise Time	t <sub>r</sub>	V <sub>GS</sub> = 10 V		20		ns
Turn-off Delay Time	t <sub>d(off)</sub>	R <sub>G</sub> = 10 Ω		39		ns
Fall Time	t <sub>f</sub>			14		ns
Total Gate Charge	Q <sub>G</sub>	V <sub>DD</sub> = 16 V		23		nC
Gate to Source Charge	Q <sub>GS</sub>	V <sub>GS</sub> = 10 V		4		nC
Gate to Drain Charge	Q <sub>GD</sub>	I <sub>D</sub> = 48 A		7		nC
Body Diode Forward Voltage	V <sub>F(S-D)</sub>	I <sub>F</sub> = 48 A, V <sub>GS</sub> = 0 V		1.1		V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 48 A, V <sub>GS</sub> = 0 V		33		ns
Reverse Recovery Charge	Q <sub>rr</sub>	di/dt = 100 A/μs		25		nC

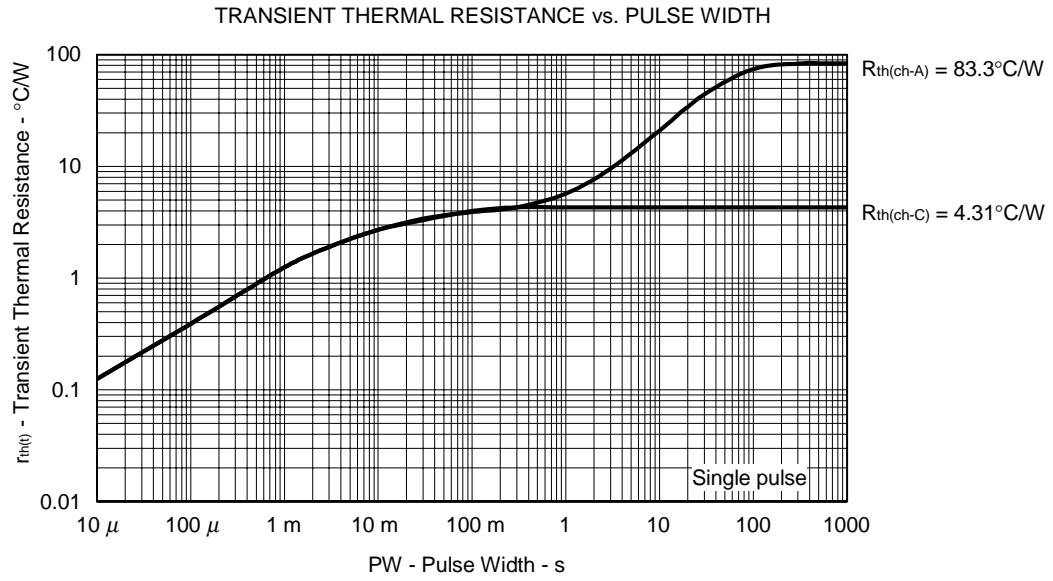
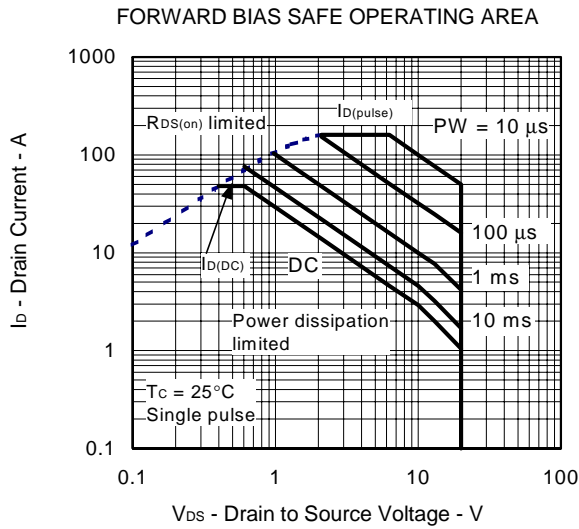
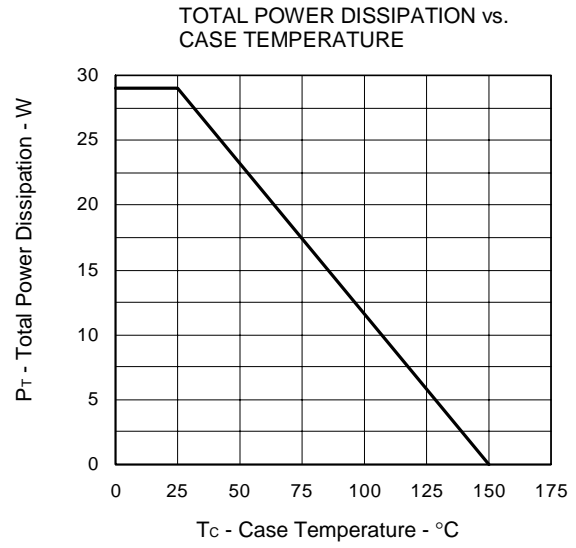
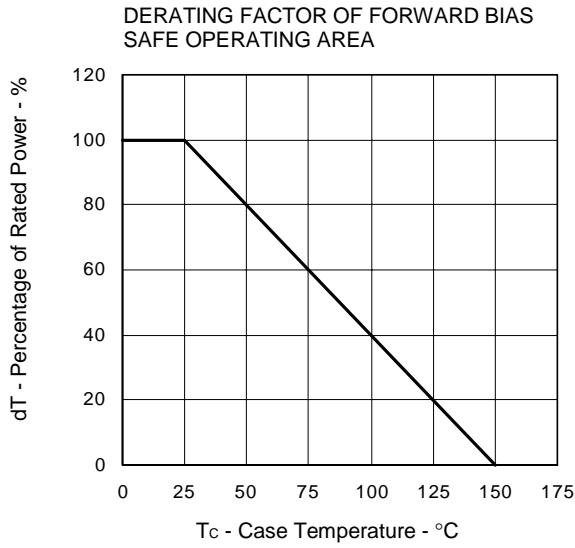
★ **TEST CIRCUIT 1 SWITCHING TIME**



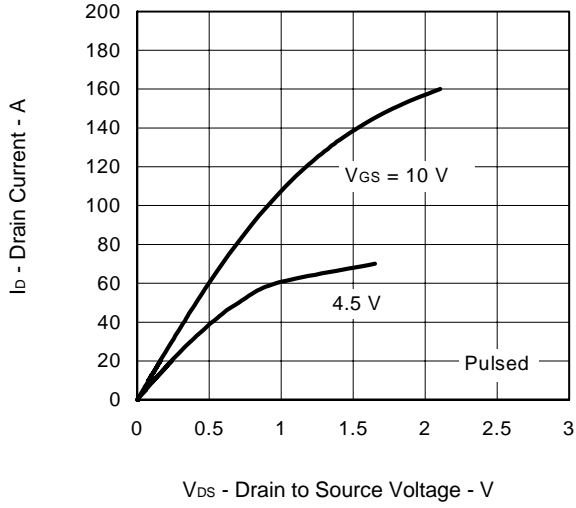
**TEST CIRCUIT 2 GATE CHARGE**



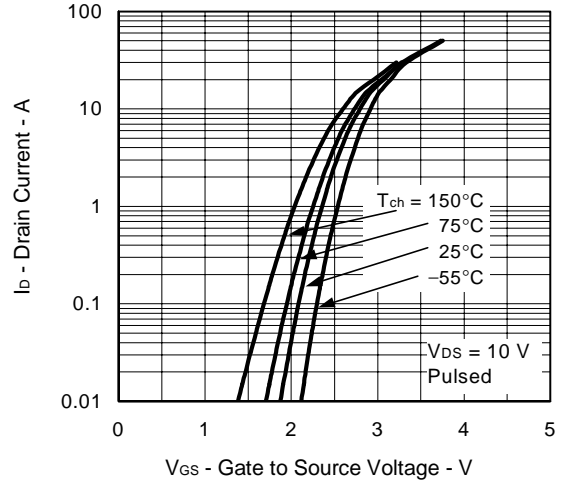
★ TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25°C)



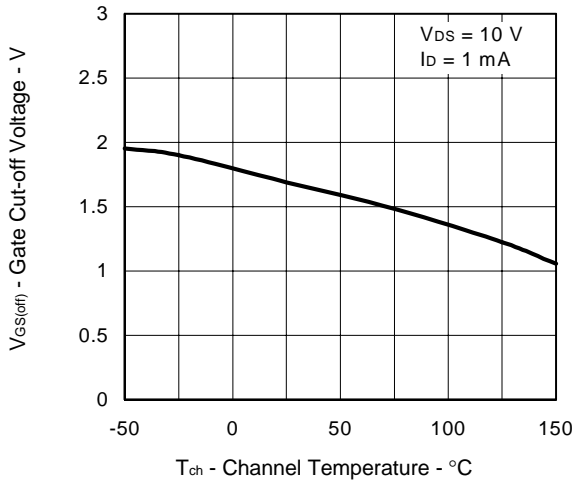
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



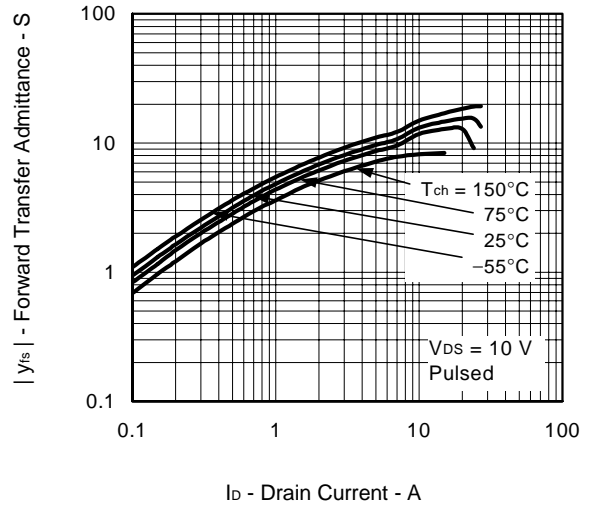
FORWARD TRANSFER CHARACTERISTICS



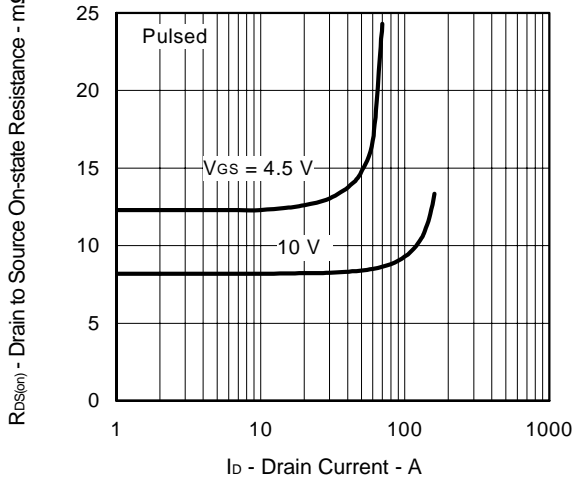
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



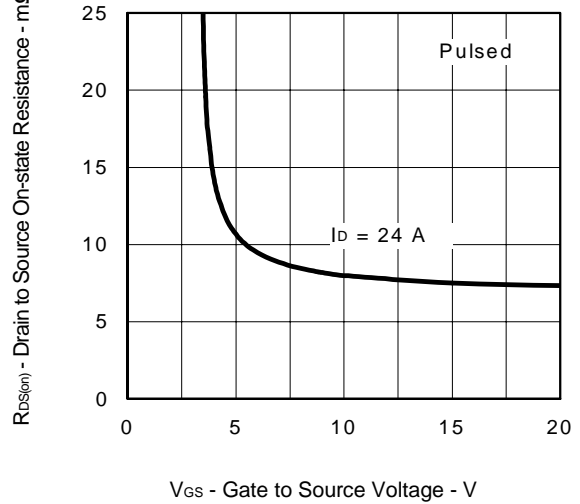
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



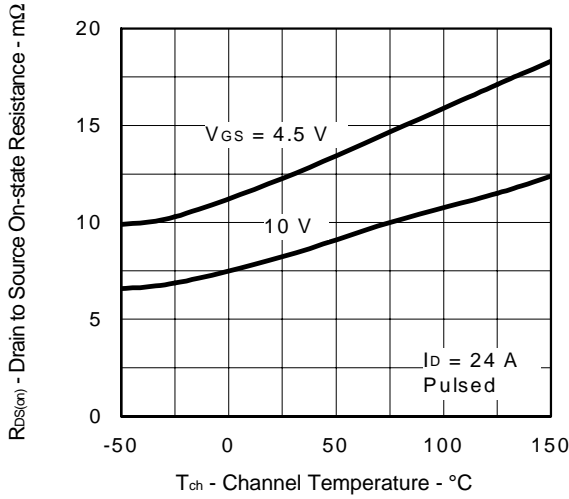
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



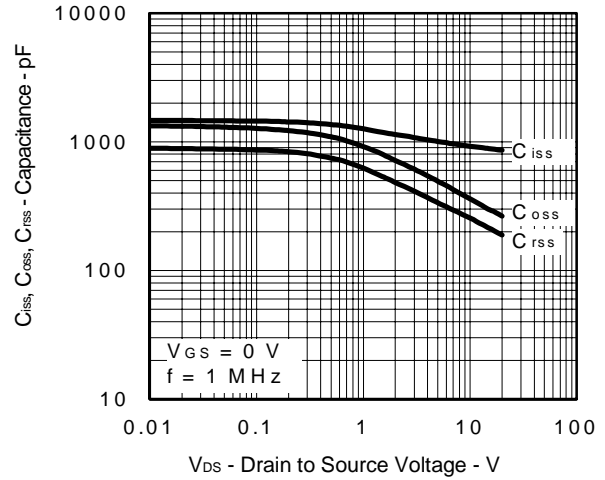
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



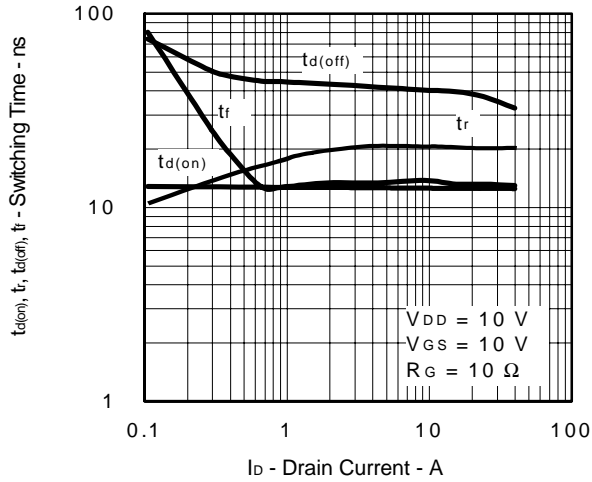
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



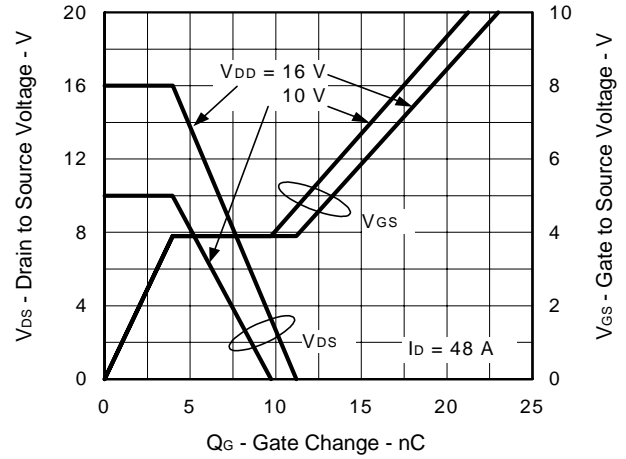
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



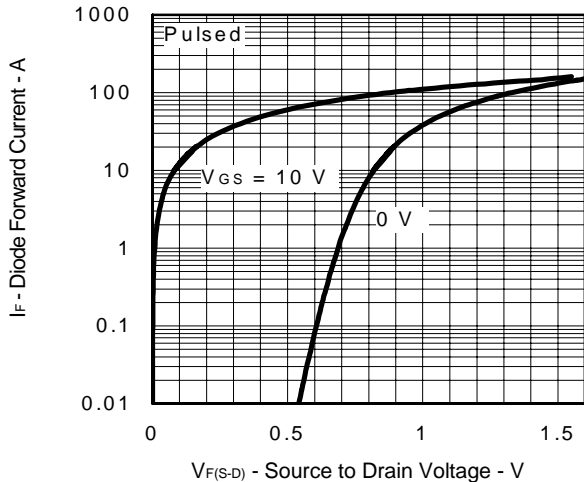
SWITCHING CHARACTERISTICS



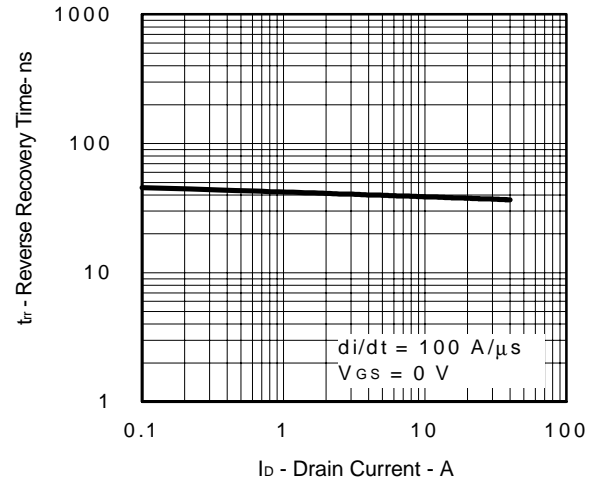
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE

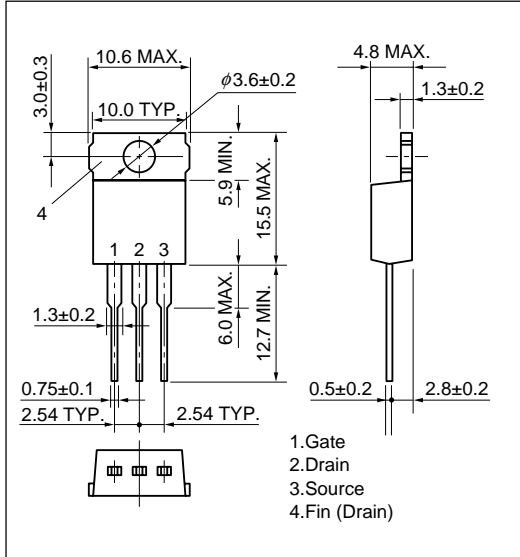


REVERSE RECOVERY TIME vs. DRAIN CURRENT

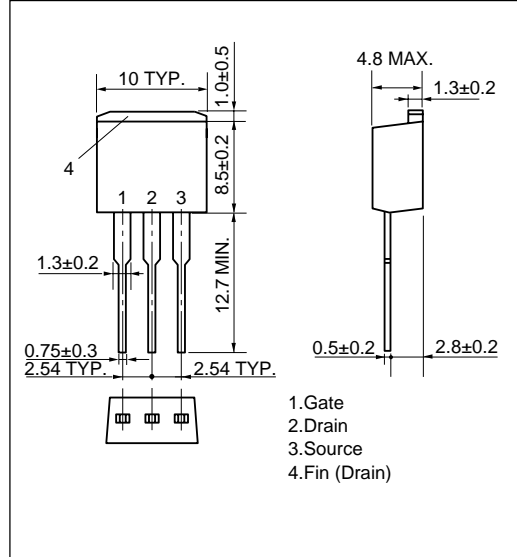


★ PACKAGE DRAWINGS (Unit: mm)

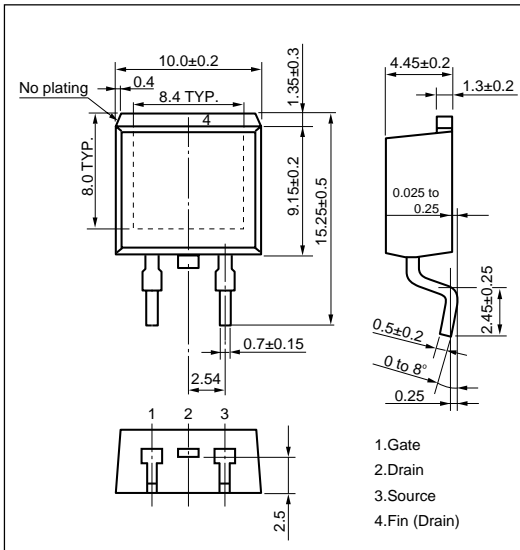
1) TO-220AB (MP-25)



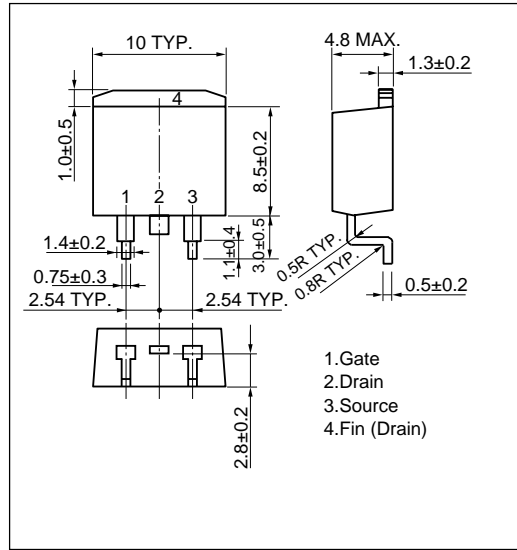
2) TO-262 (MP-25 Fin Cut)



3) TO-263 (MP-25ZK)

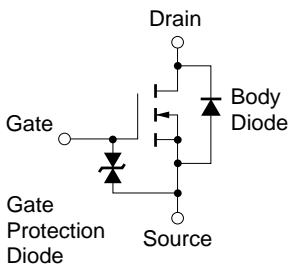


4) TO-220SMD (MP-25Z) **Note**



**Note** This package is produced only in Japan.

**EQUIVALENT CIRCUIT**



**Remark** The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.



[MEMO]

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